

SHEET 1 OF 1

Form PTO 1449  
(Modified)U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY DOCKET NO.  
240669US2SERIAL NO.  
10/624,555

## LIST OF REFERENCES CITED BY APPLICANT

## APPLICANT

Yukio TANIGUCHI, et al.

FILING DATE  
July 23, 2003GROUP  
1756

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
AR	AA	2004/0126674 A1	07/01/2004	Yukio TANIGUCHI, et al.			
	AB	2004/0061149 A1	04/01/2004	Masayuki JYUMONJI, et al.			
	AC	2003/0099264 A1	05/29/2003	Marcos DANTUS, et al.			
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	AH	6,734,635 B2	05/11/2004	Masafumi KUNII, et al.			
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## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

AR	AW	Wen-Chang YEH, et al., "Effects of a Low-Melting-Point Underlayer on Excimer-Laser-Induced Lateral Crystallization of Si Thin-Films", Jpn. J. Appl. Phys., vol. 40, no. 5A, May 2001, pages 3096-3100
AR	AX	Y. SANO, et al., "Highly Packed and Ultra-Large Si Grains Grown by a Single-Shot Irradiation of Excimer-Laser Light Pulse", Department of Physical Electronics, Tokyo Institute of Technology, 8 pages
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	AZ	

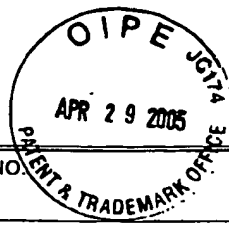
☐ Additional References sheet(s) attached

Examiner

Date Considered

6/30/05

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	AA	2004-0036969	02/26/04	TANIGUCHI et al.			
	AB	2004-0005744	01/08/04	TANIGUCHI et al.			
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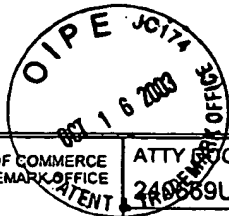
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	AW	Masakiyo MATSUMURA, "PREPARATION OF ULTRA-LARGE GRAIN SILICON THIN-FILMS BY EXCIMER-LASER", Surface Science, Vol. 21, No. 5, pp. 278-287, 2000, (pgs. 34 - 43)					
	AX	M. NAKATA, et al., "TWO-DIMENSIONALLY POSITION-CONTROLLED ULTRA-LARGE GRAIN GROWTH BASED ON PHASE-MODULATED EXCIMER-LASER ANNEALING METHOD", Department of Physical Electronics, Tokyo Institute of Technology, Electrochemical Society Proceedings Vol. 2000-31, (-5- pgs)					
	AY						
	AZ					<input type="checkbox"/> Additional References sheet(s) attached	
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	AV	W. YEH, et al., Jpn. J. Appl. Phys., vol. 41, Part 1, no. 4A, pages 1909-1914, "PROPOSED SAMPLE STRUCTURE FOR MARKED ENLARGEMENT OF EXCIMER-LASER-INDUCED LATERAL GRAIN GROWTH IN Si THIN FILMS", April 2002					
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	AY	M. MATSUMURA, et al., Thin Solid Films, vol. 337, pages 123-128, "ADVANCED EXCIMER-LASER ANNEALING PROCESS FOR QUASI SINGLE-CRYSTAL SILICON THIN-FILM DEVICES", 1999					
	AZ	M. MATSUMURA, Applied Physics, vol. 71, no. 5, pages 543-547, "EXCIMER-LASER-GROWN SILICON THIN FILMS WITH ULTRALARGE GRAINS", 2002				<input type="checkbox"/> Additional References sheet(s) attached	
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